

# MMBTA06WT1

## Driver Transistor

### NPN Silicon

Moisture Sensitivity Level: 1  
ESD Rating: Human Body Model – 4 kV  
Machine Model – 400 V

#### Features

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	80	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	500	mAdc

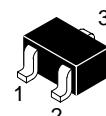
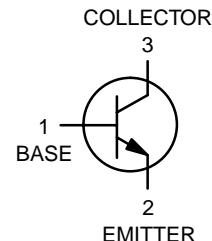
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^\circ\text{C}$	P <sub>D</sub>	150	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	833	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C



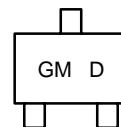
ON Semiconductor®

<http://onsemi.com>



SC-70  
CASE 419  
STYLE 3

#### MARKING DIAGRAM



GM = Specific Device Code  
D = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBTA06WT1	SC-70	3000/Tape & Reel
MMBTA06WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage (Note 1) ( $I_C = 1.0 \text{ mA DC}$ , $I_B = 0$ )	$V_{(\text{BR})\text{CEO}}$	80	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 100 \mu\text{A DC}$ , $I_C = 0$ )	$V_{(\text{BR})\text{EBO}}$	4.0	—	Vdc
Collector Cutoff Current ( $V_{CE} = 60 \text{ Vdc}$ , $I_B = 0$ )	$I_{CES}$	—	0.1	$\mu\text{A DC}$
Collector Cutoff Current ( $V_{CB} = 80 \text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	—	0.1	$\mu\text{A DC}$

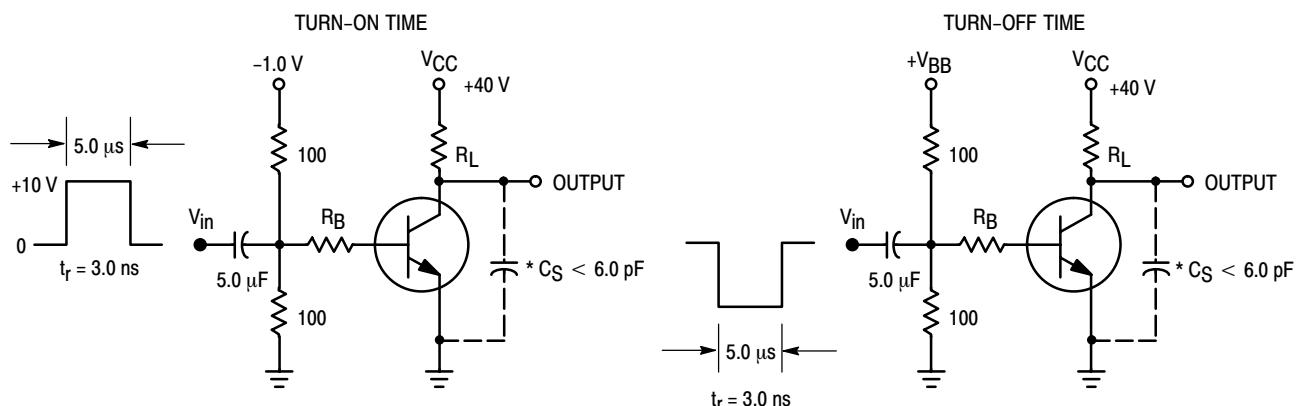
**ON CHARACTERISTICS**

DC Current Gain ( $I_C = 10 \text{ mA DC}$ , $V_{CE} = 1.0 \text{ Vdc}$ ) ( $I_C = 100 \text{ mA DC}$ , $V_{CE} = 1.0 \text{ Vdc}$ )	$h_{FE}$	100	—	—
Collector-Emitter Saturation Voltage ( $I_C = 100 \text{ mA DC}$ , $I_B = 10 \text{ mA DC}$ )	$V_{CE(\text{sat})}$	—	0.25	Vdc
Base-Emitter On Voltage ( $I_C = 100 \text{ mA DC}$ , $V_{CE} = 1.0 \text{ Vdc}$ )	$V_{BE(\text{on})}$	—	1.2	Vdc

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain - Bandwidth Product (Note 2) ( $I_C = 10 \text{ mA}$ , $V_{CE} = 2.0 \text{ V}$ , $f = 100 \text{ MHz}$ )	$f_T$	100	—	MHz
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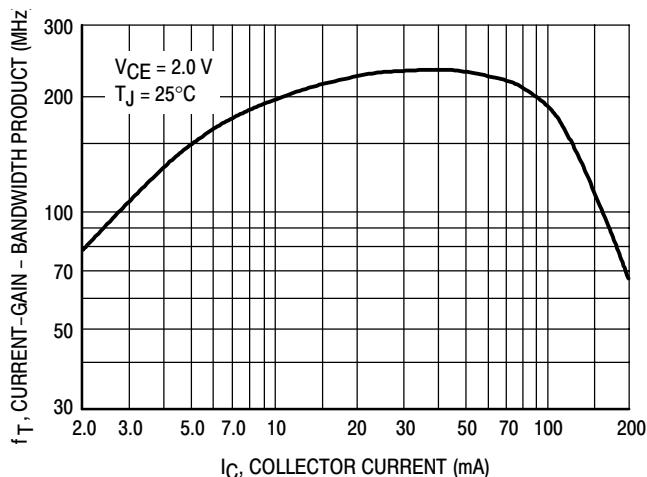
1. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .
2.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.



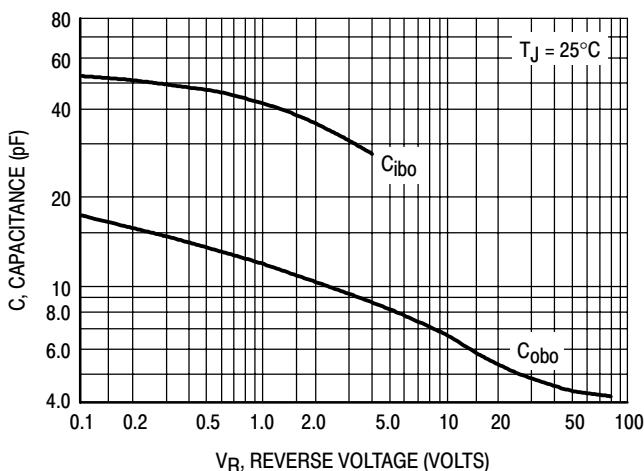
\*Total Shunt Capacitance of Test Jig and Connectors  
For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

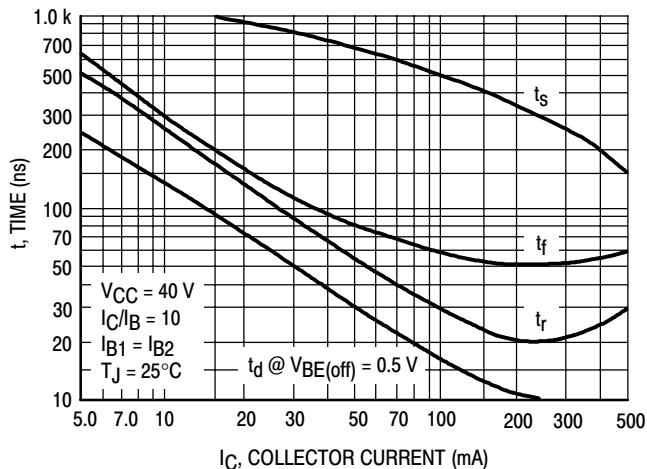
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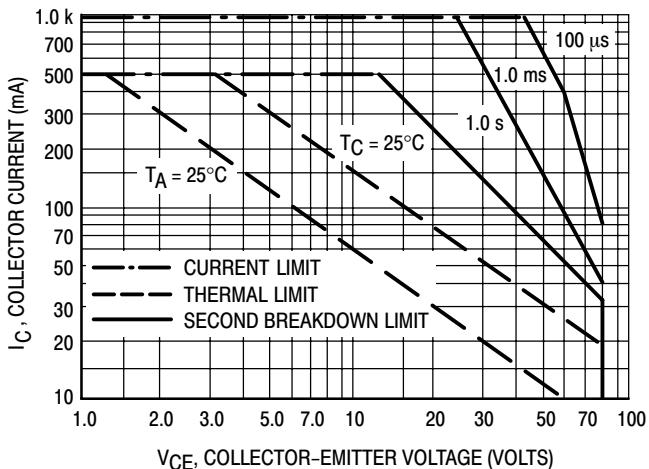
**Figure 2. Current—Gain — Bandwidth Product**



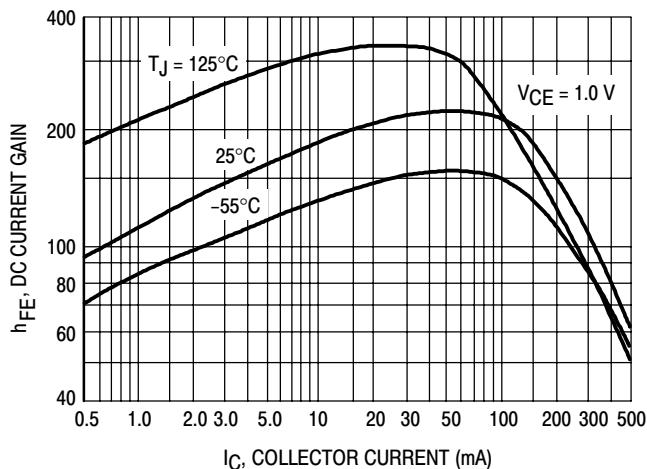
**Figure 3. Capacitance**



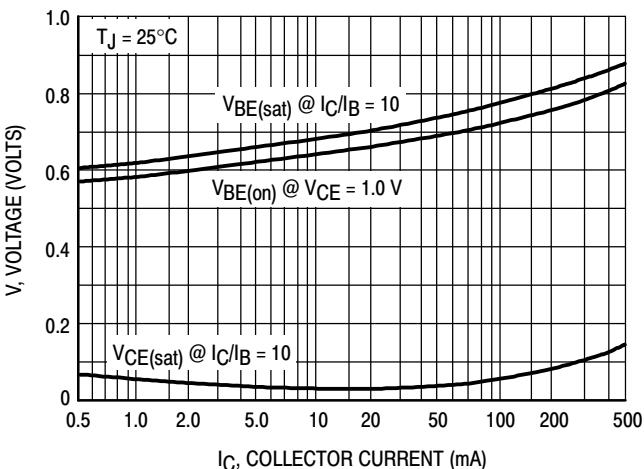
**Figure 4. Switching Time**



**Figure 5. Active—Region Safe Operating Area**

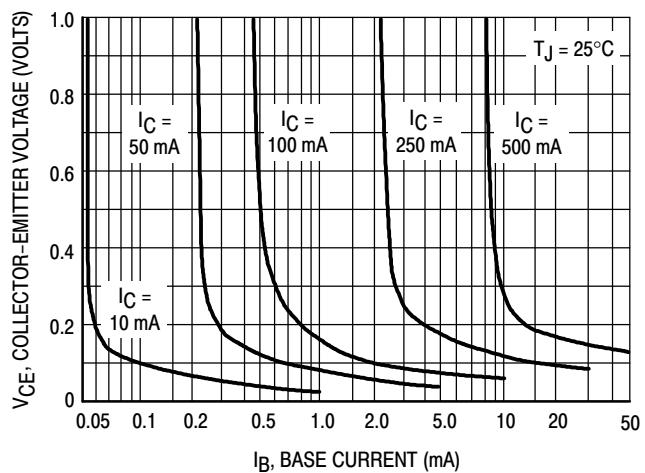


**Figure 6. DC Current Gain**

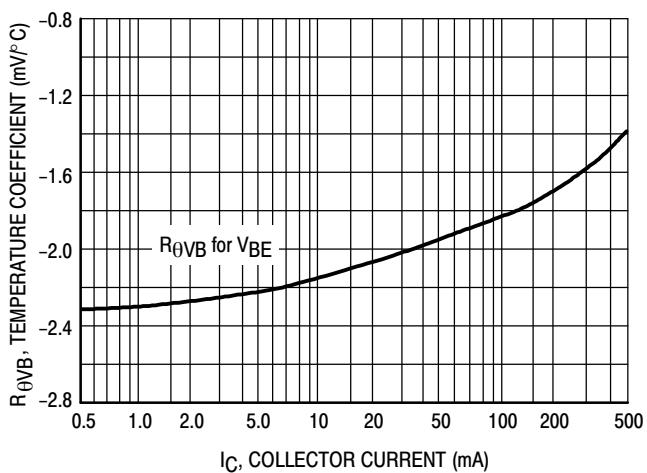


**Figure 7. "ON" Voltages**

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**Figure 8. Collector Saturation Region**



**Figure 9. Base-Emitter Temperature Coefficient**